



Upgrade of the Belle II Vertex Detector with Depleted Monolithic CMOS Active Pixel Sensors

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on behalf of the Belle II VTX collaboration

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- 3. The VTX Upgrade Proposal
- 4. The TJ-Monopix2 chip
- 5. The OBELIX sensor : Optimized Belle2 pIXel sensor
- 6. Conclusions

VTX collaboration

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The Belle II Experiment



- Located at the SuperKEKB collider in Tsukuba, Japan
- $\circ~$ Asymmetric e⁺- e⁻ collider at 4 / 7 GeV and vs = 10.58 GeV
- Luminosity frontier experiment, exploring new physics
- Target instantaneous luminosity of 6x10³⁵ cm⁻²s⁻¹, currently 0.47x10³⁵ cm⁻²s⁻¹
- Target integrated luminosity of **50** ab⁻¹, currently **0.43** ab⁻¹
 - Machine related beam background will increase with high luminosity
 - Efficiency, resolution and performance of data tracking could degrade with higher occupancy from background
 - Extrapolation to this target luminosity has large uncertainty and limited safety margins





- An upgrade of the machine elements and the detector's **interaction region (IR)** is required:
 - \circ To cope with the higher luminosity provided by the SuperKEKB accelerator
 - To improve detector robustness against high backgrounds
 - To provide larger safety factors for running at higher luminosity
 - To increase longer term subdetector radiation resistance
 - To improve overall physics performance
- A long shutdown is foreseen around early 2030 and provides the opportunity to install an upgraded detector



A new vertex detector concept VXD is proposed

The Current Vertex Detector (VXD)

- $\,\circ\,$ Current VXD performance good and operating with low background occupancy < 1 $\,\%\,$
 - $\,\circ\,$ Well below limits: PXD~3%, SVD~5%
- $\circ~$ Two different technologies compose the VXD:
 - \circ Pixel Detector (PXD)
 - $\,\circ\,\,$ Two layers of DEPFET pixel sensor
 - $\circ~$ Material budget: 0.25 % X0 / layer
 - $\circ~$ Pixel pitch: 50 to 75 μm
 - $\circ~$ Integration time of 20 μs
 - Silicon Vertex Detector (SVD)
 - $\circ~$ Four layers of double sided silicon strip sensor
 - $\circ~$ Material budget: 0.75 % X0 / layer
 - Up to 12 cm long strips
 - Time resolution of 3 ns



Silicon Vertex Detector (SVD)







The VTX Upgrade proposal

- A new fully pixelated CMOS detector to replace the VXD VTX Ο
- Improved tracking resolution and space-time granularity Ο

Radius

Ladders

Sensors

Expected hitrate*

Material budget

- Reduced material budget $\approx 2\%$ X0 instead of 3.8%X0 (sum of all layers) Ο
- 5-6 straight layers with Depleted Monolithic Active CMOS Pixel Sensors (DMAPS) process Ο

L1

14.1

б

4

19.6

0.2

L2

22.1

10

4

7.5

L3

39.1

17

7

5.1

- L1 and L2 (iVTX) Ο
 - All silicon ladders \cap
 - Air cooling (constrains power) Ο
- L3 to L5 (oVTX) 0
 - Carbon fiber support frame Ο
 - Cold plate with liquid cooling Ο

L4

89.5

40

16

1.2

L5

140.0

31

 2×24

0.7



Unit

mm

per ladder

MHz/cm²









The VTX detector mechanics

- iVTX Inner Layers Concept:
 - 4 contiguous sensors diced as a block from the wafer
 - Flex print cables
 - Redistribution layer for interconnection
 - Heterogeneous thinning for thinness and stiffness

chips

Carbon Fiber support



Schematic view of the iVTX ladder design

oVTX Outter Layers Concept:

• Ladder structure design inspired by ALICE ITS2, composed of:

- Carbon Fiber support structure (truss)
- Cold-plate with pipes for liquid coolant circulation
- $\circ~$ Chip and Flex circuit for power and signal glued on top



• A same monolithic CMOS pixel sensor chip for all layers : **Optimized Belle II pIXel sensor (OBELIX)**

Flex circuit

Cold plate



The TJ-Monopix2 (TJM2) as prototype







TJ-Monopix2 sensor bonded on a test board

- Developed for ATLAS experiment
 - FE derived from ALPIDE
 - 4 FE flavors
 - Column-drain R/O architecture
- DMAPS Tower Semiconductor 180 nm CMOS
- \circ 2×2 cm² chip: 512×512 pixels
- $\circ~$ Pixel pitch: 33.04×33.04 μm^2
- Expected from design (simulations):
 - $\circ~\sim$ 100 e– min. threshold
 - 5-10 e– threshold dispersion (tuned)
 - \circ >97% efficiency at 10¹⁵ n_{eq} /cm²
 - \circ ~ 5 e- noise
 - \circ Fully efficient with hit rate 120 MHz/cm²
 - \circ Power: ~ 1 μ W/pixel

Base-line option for OBELIX design





The TJM2 Testing



- Characterisation of TJ-Monopix2 (all FE) to validate key performance crucial for OBELIX design
- Full characterisation on bench:
 - Threshold scans (lowest value, dispersion)
 - \circ Noise testing
 - ToT (Time Over Threshold) calibration
- Control and data acquisition system based on the BDAQ53 setup



TJM2 setup DAQ inherited from RD53 collaboration



- Typical settings for operational threshold:
 - $\circ~$ Thresholds between 200 to 300 e–
 - Average noise varies from 7 to 8 e-
- Time Over Threshold (ToT) calibration, Fe55
- o Comparison with measurement and simulations
 - Measurement from monitoring pixels of the analog output signal after the FE amplifier



The TJM2 Testing



• Full characterisation@DESY:

- Efficiency/Resolution measurements
- Radiation hardness (NIEL and TID irradiation campaigns in progress)

• Several test beam campaigns (3-5 GeV e-)

- July 2022: Non-irradiated chips
 - High threshold (500 e-)
 - $\circ~$ Hit efficiency \sim 99.54%, Cluster position residuals \sim 9 μm
- $\circ~$ July 2023: Irradiated chips at 5x10^{14} \, n_{eq}^{}/cm^2
 - $\circ~$ Lower threshold \sim 250-300 e-
 - Good performance and high efficiency
- \circ July 2024: Irradiated chips at 5x10¹⁴ n_{eq}/cm², TID of 100 Mrad
 - Good efficiency but temperature influence



Another test beam planned for 2025



Setup for testbeam – @Desy



The OBELIX Sensor

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Sensor specifications:

- Tower Semiconductor 180 nm CMOS
- Hit rate up to 120MHz/cm²
- TID tolerance: 100 MRad
- \circ NIEL tolerance: 5x10¹⁴ n_{eq}/cm²/year
- \circ Spatial resolution < 15 μ m
- Power < 200 mW/cm²
- Time precision < 100 ns
- $\circ~$ Trigger at 30kHz average frequency with 5-10 μs latency



- 464 rows and 896 columns
- Overall sensor dimensions around 30.2x18.8 mm²
- $\circ~$ Pixel pitch 33x33 μm^2
- Main design is based on the TJM2 chip







Analog

- Pixel matrix adapted from TJM2
- Column drain architecture
- Monitoring ADC
- Temperature sensors

Power pads

- Power regulators added
- Simplified system integration

Digital Periphery

- Main clk-in: 170MHz
- New end-of-column adapted to Belle II trigger
- Timestamped hits stored in memories
- Read-out when timestamp matched with trigger
- Single output at 340 MHz average bandwidth
- RD53 control/readout protocol



- The OBELIX sensor inherits the performance of the pixel matrix from TJ-Monopix2 sensor
- $\circ~$ The same pitch, 33 \times 33 μm^2 , with the same layout for the analog and digital parts
- The Matrix pixel of TJ-Monopix2 is composed of 4 pixel flavors with differences in the Front-End (FE) amplifier and detector input coupling (AC or DC):
 - Normal FE / Cascode FE
 - HV Cascode FE / HV FE
 - Based on current characterization and simulation results, 2
 FE flavors are chosen for OBELIX on equal area:
 - \circ Cascode FE
 - $\circ ~~ \text{HV Cascode FE}$



Floorplan of TJM2 sensor





The OBELIX Power management





- Power distribution is a major concern as OBELIX is larger than TJ-Monopix2, leading to performance degradation
- Long linear ladders voltage drop across ladder
- On chip regulators are being developed in OBELIX to compensate the voltage drop and minimize the material budget dedicated to power distribution:
 - Two analog LDO (Low Dropout) regulators will be implemented to supply the matrix from both sides
 - A digital LDO in the bottom side of the chip to supply the digital blocs
 - A preregulator to supply LDO references generator
 - A VPC (Voltage pre-charge) LDO to reset and recharge bit-lines between each read cycle
- The LDO generates the output voltage of 1.8 V ± 10% necessary for the technology to power the chip
- Wide input supply voltage range of 2V to 3 V







- New modules related to the Belle II trigger:
 - $\circ~$ TRU: The Trigger Unit
 - Pixel readout, trigger processing
 - $\circ~$ PTD: Periphery Time to Digital
 - $\circ~$ TTT: The Track Trigger Transmission
 - Fast transmission in parallel to the Belle II trigger system

- SCU sync & clk divider: digital clk divider, synchronize circuit & clk divider, RxDat format conversion, main function: clock divider, Rx_data SIPO synchronization
- CRU Control Unit: Implementation RD53B interface, which almost keeps the same design as TJM2, main functions: command decoder, global configuration
- **TRU Trigger Unit**: Manage pixel data from the matrix-EOC and wait for the trigger to pick them for output
- **TXU TX Unit**: generate output data and sequential output, main functions: data framing, serializer





- The SuperKEKB collider is considering a major upgrade to reach a high luminosity
- Reaching the target peak luminosity requires an upgrade of the interaction region and the Vertex Detector
- \circ A new DMAPS VTX is foreseen to improve the performance of the Belle II vertex detector
- The OBELIX sensor based on TJM2 chip with TJ180 nm technology is under development with additional features (all on-chip):
 - Voltage regulators
 - ADC and temperature sensors
 - $\,\circ\,\,$ Trigger logic, up to 10 μs latency at 120 MHz/cm²
 - Precision timing module
 - Fast transmission for trigger contribution
- Lab testing and TB campaigns on TJM2 to validate key performance crucial for OBELIX design
- Development and verification of OBELIX are entering the final stages
- Aiming submission of first version of OBELIX sensor in Spring 2025





Thanks for your attention

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